

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	40	wicker near guy.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	316	lowrey near tyler.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	52	chiang near chien.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	30	xu near daniel.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	3805	(electrode) near25 ((phase near change) or (programmable))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L7	7	(electrode) near25 ((phase near change) or (programmable)) near15 (contact near area) near15 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L6	71	(electrode) near25 ((phase near change) or (programmable)) near15 (contact near area)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040087076 A1	Reduced area intersection between electrode and programming element
2			US 20030203555 A1	Reduced area intersection between electrode and programming element
3			US 20030003691 A1	Reduced area intersection between electrode and programming element
4			US 20030003647 A1	Reduced area intersection between electrode and programming element
5			US 6673700 B2	Reduced area intersection between electrode and programming element
6			US 6605527 B2	Reduced area intersection between electrode and programming element
7			US 20030189200 A	Low heat loss and small contact area electrode structure for phase change media memory device, comprises substrate, composite electrode with dielectric mandrel, dielectric layers, phase change media, and electrode